



### Complementary Enhancement Mode MOSFET - ESD Protected

Voltage

20 / -20V

Current

0.5A / -0.5A

#### **Features**

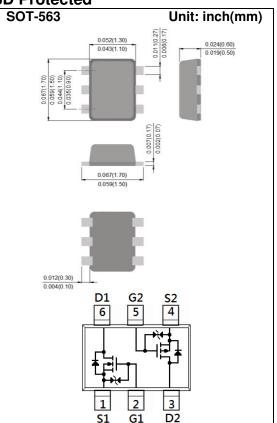
- Low Voltage Drive (1.2V)
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: SOT-563 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0026 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	20	-20	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 10 <u>+</u> 10		V
Continuous Drain Current		ID	0.5	-0.5	Α
Pulsed Drain Current(Note 4)		I <sub>DM</sub>	1.0	-1.0	Α
Power Dissipation	T <sub>a</sub> =25°C		300 2.4		mW
	Derate above 25°C	P <sub>D</sub>			mW/°C
Operating Junction and Storage Ter	$T_{J}$ , $T_{STG}$	-55~150		°C	
Typical Thermal Resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>θJA</sub>	417		°C/W





# N-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> = 250uA	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = 250uA	0.3	0.64	0.9	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 500mA	-	0.31	0.4	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 200mA	-	0.36	0.65	
		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 100mA	-	0.43	0.8	
		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 50mA	-	0.51	1.2	
		V <sub>GS</sub> = 1.2V, I <sub>D</sub> = 20mA	-	0.71	3.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 16V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	Igss	V <sub>GS=<u>+</u>8V, V<sub>DS</sub>=0V</sub>	-	<u>+</u> 0.5	<u>+</u> 10	uA
Dynamic <sup>(Note 5)</sup>						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =500mA, V <sub>GS</sub> =4.5V	-	1.4	-	nC pF
Gate-Source Charge	$Q_{gs}$		-	0.22	-	
Gate-Drain Charge	$Q_{gd}$		-	0.21	-	
Input Capacitance	Ciss	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	67	-	
Output Capacitance	Coss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,	-	19	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	6	-	
Turn-On Delay Time	td <sub>(on)</sub>	V 40V L 450 A	-	2.8	-	ns
Turn-On Rise Time	tr	V <sub>DD</sub> =10V, I <sub>D</sub> =150mA, V <sub>GS</sub> =4V,	-	20	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	23	-	
Turn-Off Fall Time	tf	$R_G=10\Omega^{(Note\ 1,2)}$	-	23	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					500	А
Diode Forward Current	Is		-	-	500	mA
Diode Forward Voltage	V <sub>SD</sub>	Is= 500mA, V <sub>GS</sub> =0V	-	0.87	1.3	V





### **P-Channel Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.3	-0.6	-1.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-500mA	-	0.9	1.2	_
		V <sub>GS</sub> =-2.5V,I <sub>D</sub> =-200mA	-	1.07	1.5	
		V <sub>GS</sub> =-1.8V,I <sub>D</sub> =-100mA	-	1.25	2.2	Ω
		V <sub>GS</sub> =-1.5V,I <sub>D</sub> =-40mA	-	1.42	3.6	-
		V <sub>GS</sub> =-1.2V,I <sub>D</sub> =-10mA	-	1.7	6.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-16V,V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	Igss	V <sub>GS=<u>+</u>8V,V<sub>DS</sub>=0V</sub>	-	<u>+</u> 2	<u>+</u> 10	uA
Dynamic <sup>(Note 5)</sup>						
Total Gate Charge	Qg	V <sub>DS</sub> =-10V, I <sub>D</sub> =-500mA, V <sub>GS</sub> =-4.5V	-	1.4	-	nC
Gate-Source Charge	Qgs		-	0.19	-	
Gate-Drain Charge	$Q_{gd}$		-	0.2	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V,	-	38	-	pF
Output Capacitance	Coss		-	15	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	9	-	
Turn-On Delay Time	td <sub>(on)</sub>	101/ 1 500 4	-	7.2	-	
Turn-On Rise Time	tr	V <sub>DD</sub> =-10V, I <sub>D</sub> =-500mA, V <sub>GS</sub> =-4.5V,	-	21	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	85	-	
Turn-Off Fall Time	tf	$R_G=6\Omega^{(Note 1,2)}$	_	116	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	Is		_		-500	mA
Diode Forward Current	15		_	_	-300	1117
Diode Forward Voltage	$V_{SD}$	Is=-500mA, V <sub>GS</sub> =0V	-	-0.9	-1.3	V

### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### N-Channel TYPICAL CHARACTERISTIC CURVES

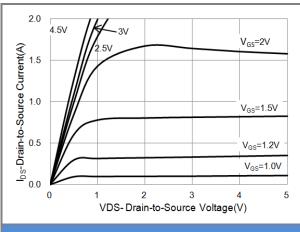


Fig.1 On-Region Characteristics

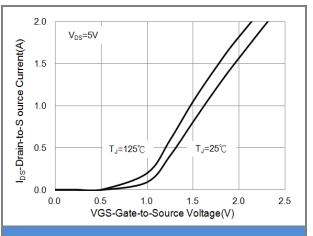


Fig.2 Transfer Characteristics

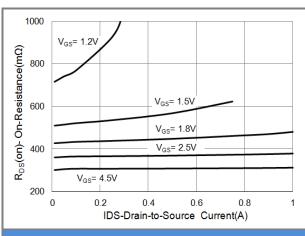


Fig.3 On-Resistance vs. Drain Current

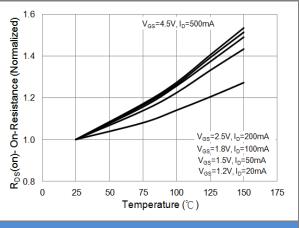
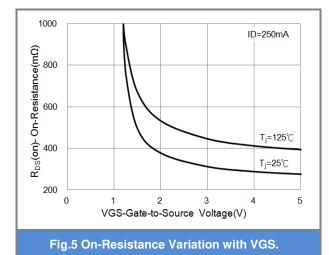
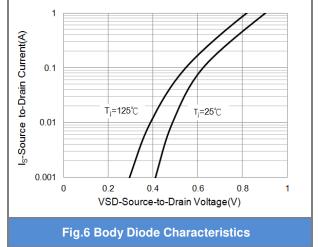


Fig.4 On-Resistance vs. Junction temperature

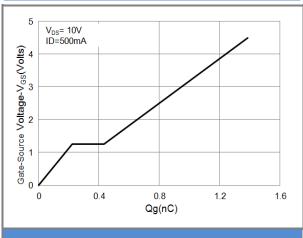








#### **N-Channel TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

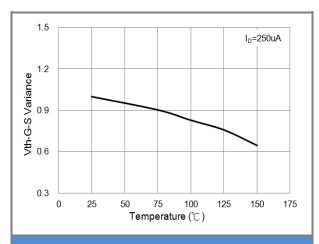


Fig.8 Threshold Voltage Variation with Temperature.

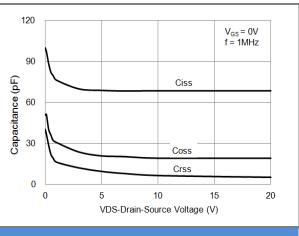


Fig.9 Capacitance vs. Drain-Source Voltage.





#### P-Channel TYPICAL CHARACTERISTIC CURVES

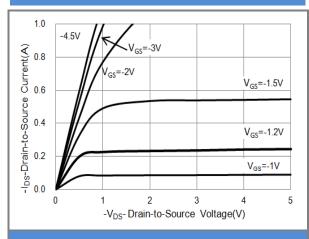


Fig.1 On-Region Characteristics

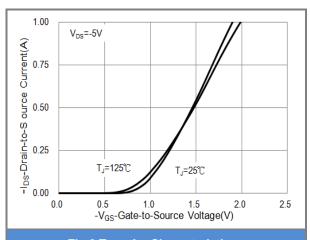


Fig.2 Transfer Characteristics

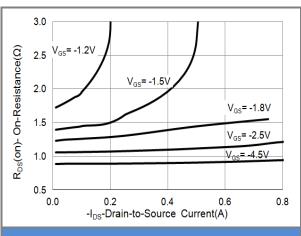


Fig.3 On-Resistance vs. Drain Current

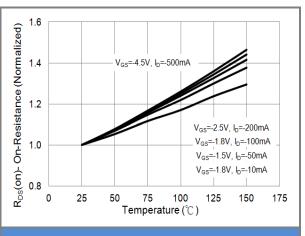
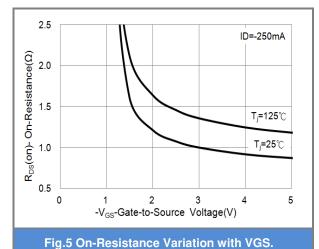


Fig.4 On-Resistance vs. Junction temperature



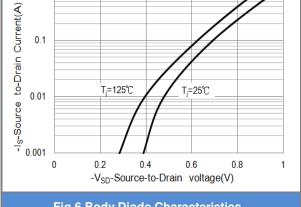


Fig.6 Body Diode Characteristics





### P-Channel TYPICAL CHARACTERISTIC CURVES

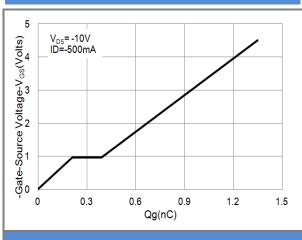


Fig.7 Gate-Charge Characteristics

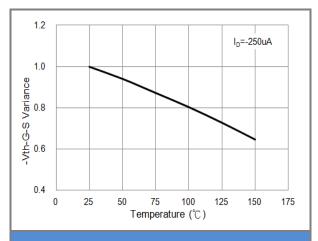


Fig.8 Threshold Voltage Variation with Temperature.

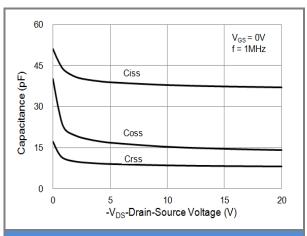


Fig.9 Threshold Voltage Variation with Temperature.

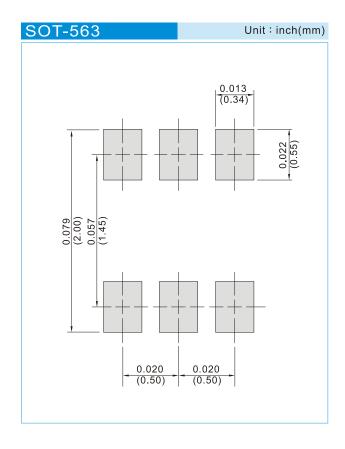




### PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJX8601_R1_00001	SOT-563	4K pcs / 7" reel	X61	Halogen free RoHS compliant

### **MOUNTING PAD LAYOUT**







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